

ZXTN5551G

160V, SOT223, NPN high voltage transistor

Summary

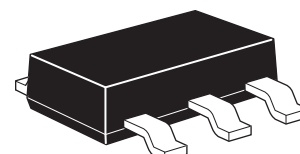
$BV_{CEO} > 160V$

$BV_{EBO} > 6V$

$I_{C(cont)} = 600mA$

$P_D = 2W$

Complementary part number ZOTP5401G

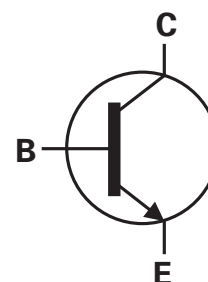


Description

A high voltage NPN transistor in a high power dissipation surface mount package

Features

- 160V rating
- SOT223 package

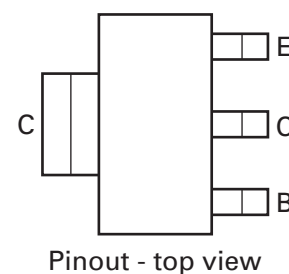


Applications

- High voltage amplification

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN5551GTA	7	12	1000
ZXTN5551GTC	13	12	4000



Device marking

ZXTN
5551

ZXTN5551G

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	180	V
Collector-emitter voltage	V_{CEO}	160	V
Emitter-base voltage	V_{EBO}	6	V
Continuous collector current ^(a)	I_C	600	mA
Power dissipation at $T_A = 25^{\circ}\text{C}^{(a)}$	P_D	2	W
Linear derating factor		16	mW/ $^{\circ}\text{C}$
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance

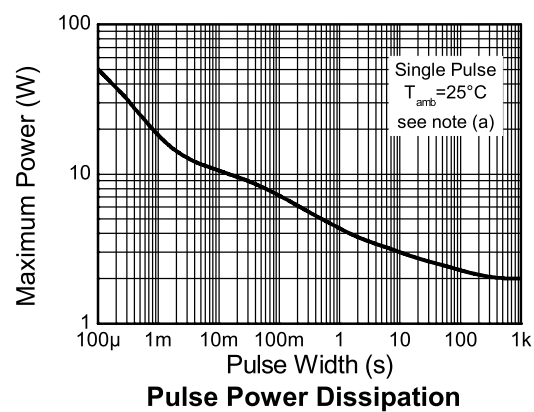
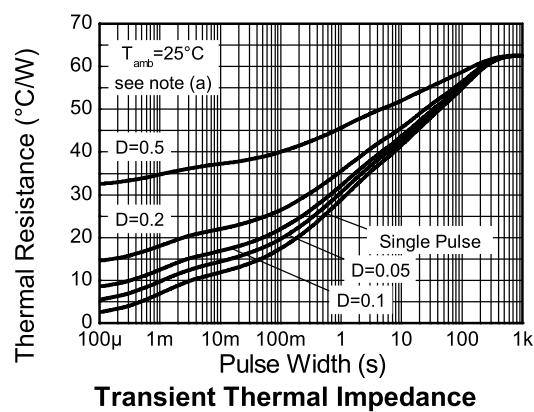
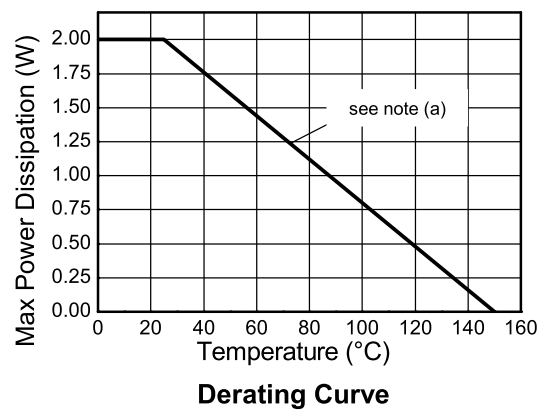
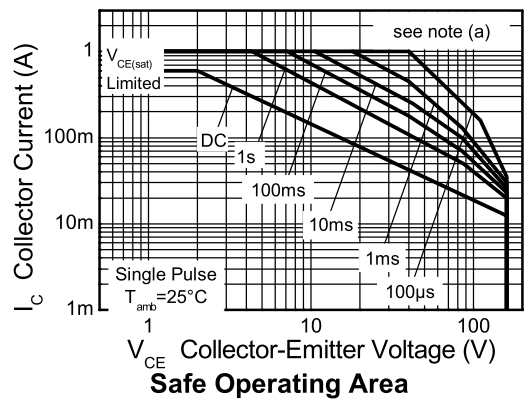
Parameter	Symbol	Value	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	62.5	$^{\circ}\text{C/W}$

NOTES:

(a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

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Characteristics



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Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

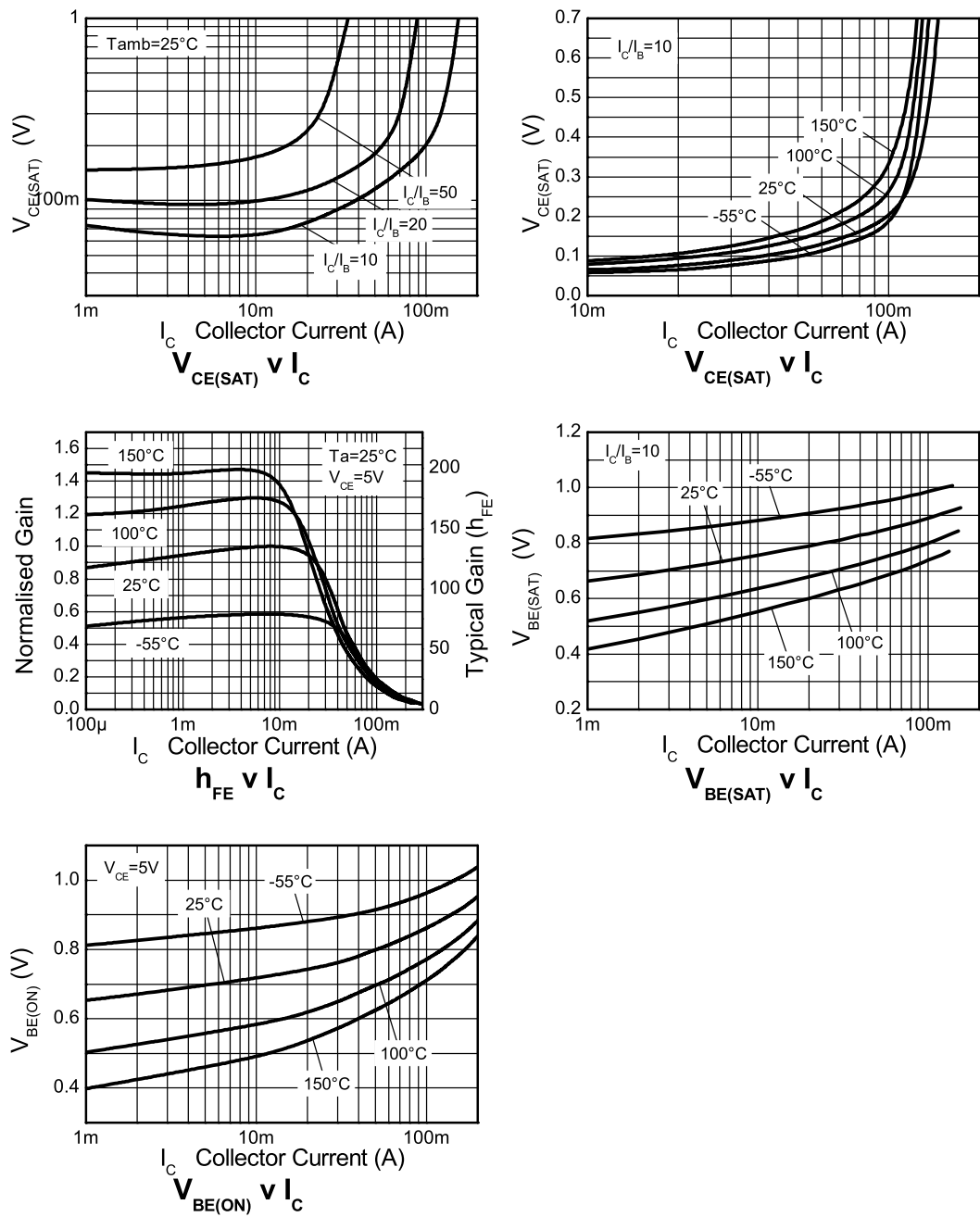
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	180	270		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	160	200		V	$I_C = 1\text{mA}^{(*)}$
Emitter-base breakdown voltage	BV_{EBO}	6	7.85		V	$I_E = 10\mu\text{A}$
Collector cut-off current	I_{CBO}		<1	50 50	nA μA	$V_{CB} = 120\text{V}$ $V_{CB} = 120\text{V}, T_{amb} = 100^{\circ}\text{C}$
Collector-emitter saturation voltage	$V_{CE(Sat)}$		65 115	150 200	mV mV	$I_C = 10\text{mA}, I_B = 1\text{mA}^{(*)}$ $I_C = 50\text{mA}, I_B = 5\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(Sat)}$		760 840	1000 1200	mV mV	$I_C = 10\text{mA}, I_B = 1\text{mA}^{(*)}$ $I_C = 50\text{mA}, I_B = 5\text{mA}^{(*)}$
Static forward current transfer ratio	h_{FE}	80 80 30	135 140 65	250		$I_C = 1\text{mA}, V_{CE} = 5\text{V}^{(*)}$ $I_C = 10\text{mA}, V_{CE} = 5\text{V}^{(*)}$ $I_C = 50\text{mA}, V_{CE} = 5\text{V}^{(*)}$
Transition frequency	f_T		130		MHz	$I_C = 10\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}			6	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}^{(*)}$
Small signal	h_{FE}	50		260		$I_C = 10\text{mA}, V_{CE} = 10\text{V},$ $f = 1\text{kHz}^{(\dagger)}$
Delay time	$t_{(d)}$		95		ns	$V_{CC} = 10\text{V}, I_C = 10\text{mA},$ $I_{B1} = I_{B2} = 1\text{mA}$
Rise time	$t_{(r)}$		64		ns	
Storage time	$t_{(s)}$		1256		ns	
Fall time	$t_{(f)}$		140		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

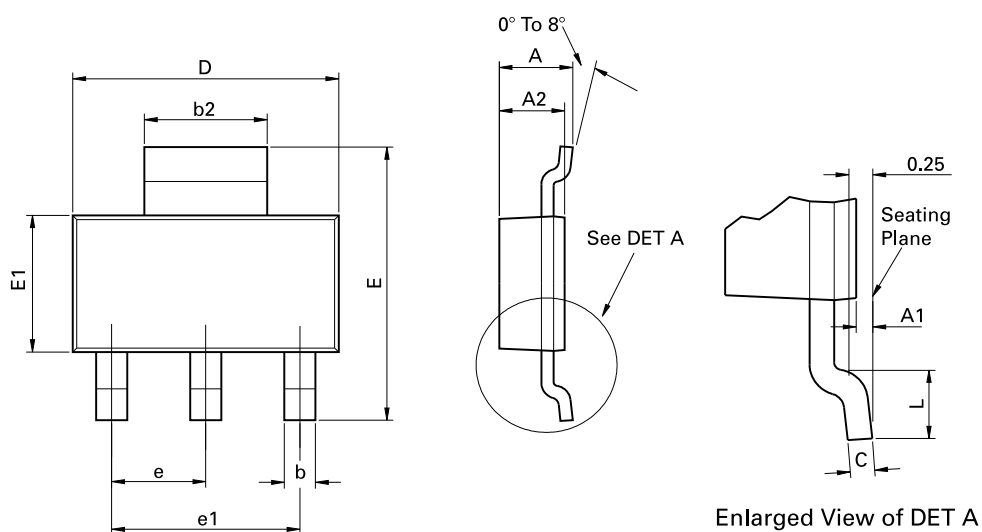
(†) Periodic sample test only.

Typical Characteristics



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Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	e	2.30 BSC		0.0905 BSC	
A2	1.55	1.65	0.0610	0.0649	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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